

KG1000A-D

HIGH FREQUENCY THYRISTOR

Features

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Short turn-off time and low switching losses
- Hermetic metal cases with ceramic insulators

Application

- Inductive heating
- Electronic welders
- Self-commutated inverters
- AC motor speed control
- General power switching applications

$I_{T(AV)}$	1000A
V_{DRM}/V_{RRM}	800-1400 V
t_q	6~15 μ s
I_{TSM}	12KA

Symb.		parameter	Test Conditions	T_J ($^{\circ}$ C)	Value	Unit
Current Ratings	$I_{T(AV)}$	average on-state current	180°half sine wave 50Hz Double side cooled $T_{hs}=55^{\circ}$ C	115	1000	A
			50Hz			
	I_{TSM}	Surge on-state current	10ms half sine wave $VR=0.6V_{RRM}$	115	8	KA
I^2t	I^2t for fusing coordination	115		720	KA ² S	
Characteristics	V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	V_{DRM} & V_{RRM} $t_p=10ms$ V_{DSM} & $V_{RSM}=V_{DRM}$ & $V_{RRM}+100V$	115	800-1400	V
	I_{DRM} I_{RRM}	Repetitive peak current	$V_{DM}=V_{DRM}$ $V_{RM}=V_{RRM}$	115	Max.100	mA
	V_{TO}	Threshold voltage		115	Max.1.63	V
	V_{TM}	Peak on-state voltage	$I_{TM}=3000A$, $F=26KN$	25	Max.3.2	V
	r_T	On-state slop resistance		115	Max.0.25	m Ω
	I_H	Holding current	$V_A=12V$, $I_A=1A$	25	20-400	ma
Dynamic Parameters	dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	115	Max.200	V/ μ s
	di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$ to 1000A, Gate pulse $t_r \leq 0.5\mu s$ $I_{GM}=1.5A$	115	Max.250	A/ μ s
	t_q	Circuit commutated turn-off time	$I_{TM}=800A$, $t_p=1000\mu s$, $V_R=50V$, $di/dt=-20A/\mu s$	115	6-15	μ s
	I_{TM}	Reserse recovery current	$TM=800A$, $t_p=1000\mu s$, $V_R=50V$	115	Typ.60	
	t_{Tr}	Reverse recovery time	$dv/dt=30V/\mu s$, $di/dt=-20A/\mu s$	115	Typ.3.5	μ s

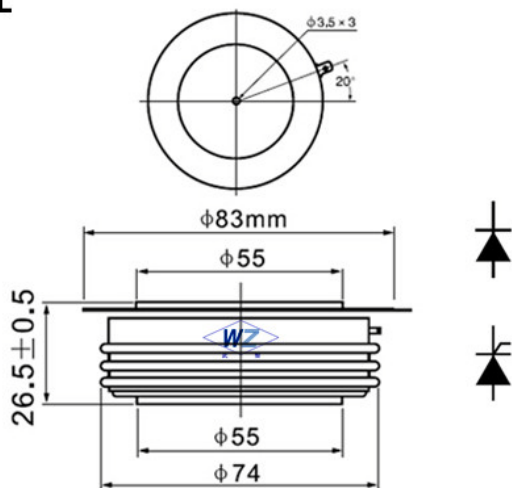
	Q_{rr}	Recovery charge		115	Typ.105 Max.120	μc
Gate Parameters	I_{GT}	Gate trigger current	$V_A=12V, I_A=1A$	25	30-300	mA
	V_{GT}	Gate trigger voltage		25	0.8-3.0	V
	V_{GD}	Non-trigger gate voltage	$V_{DM}=67\% V_{DRM}$	115	Min.0.3	V

Thermal & Mechanical Date

Symb.	parameter	Test Conditions	Value	Unit
$R_{th(j-h)}$	Thermal resistance Junction to heat sink	Double side cooled, mounting force 26KN	0.022	$^{\circ}C/W$
F_m	Mounting force		21-30	KN
T_{stg}	Stored temperature		-40-+140	$^{\circ}C$
W_t	Weight		620	g

Dimensions:

C21



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